

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

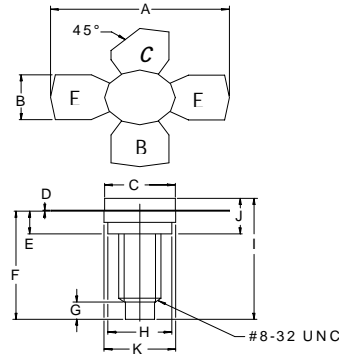
The **ASI 2SC2893** is Designed for use in UHF amplifiers up to 400 MHz.

**FEATURES:**

- $P_{OUT} = 10.7$  W Typical at 400 MHz
- **Omnigold™** Metallization System

**MAXIMUM RATINGS**

$I_C$	1.5 A
$V_{CB}$	55 V
$V_{CE}$	32 V
$V_{EB}$	3.0 V
$P_{DISS}$	22 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	8.0 °C/W

**PACKAGE STYLE .280 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 60$ mA	32			V
$BV_{CES}$	$I_C = 8.0$ mA $V_{BE} = 0$ V	55			V
$I_{EBO}$	$V_{CE} = 2.0$ V			500	$\mu$ A
$I_{CBO}$	$V_{CB} = 30$ V			500	$\mu$ A
$h_{FE}$	$V_{CE} = 10$ V $I_C = 400$ mA	20		200	---
$C_{ob}$	$V_{CB} = 28$ V $f = 1.0$ MHz		10	15	pF
$P_{out}$	$V_{CE} = 28$ V $I_C = 400$ mA $f = 400$ MHz	7.9	10.7		W
$\eta_c$	$P_{IN} = 0.63$ W	55	65		%